⟨Field-Effect Transistor⟩

2SK2881

For Low Frequency Amplify Application
N Channel Junction type Micro(Frame type)

DESCRIPTION

2SK2880 is a small type resin sealed N channel junction type FET. It is especially designed for low frequency low noise amplify application.

FEATURE

- · Low noise figure NF=1dB (typ) (VDS=10V,ID=1mA,RG=1kΩ,f=100Hz)
- High | yfs | yfs |=8mS(typ) (VDs=10V,ID=1mA,f=1KHz)
- · Low RDS(ON)

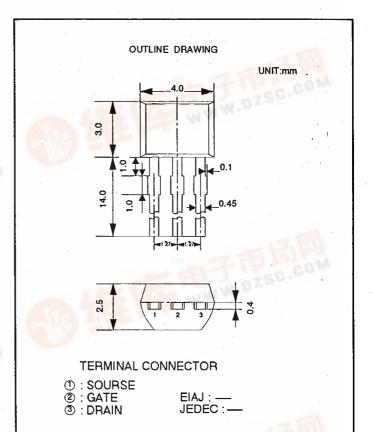
RDS(ON)=70 Ω (typ)

· High voltage

VgDo=Vgso=-50V

APPLICATION

Low frequency voltage amplify, analog switch.



MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	RATINGS	UNIT
Vgdo	Gate to Drain voltage	-50	V
Vgso	Gate to Source voltage	-50	V
ΙD	Drain current	20	mA
l G	Gate current	10	mA
PT	Total allowable dissipation	450	mW
Tch	Channel temperature	+125	°C
Tstg	Storage temperature	-55to+125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	TESTCONDITIONS	LIMITS			
		MIN	TYP	MAX	UNIT
Gate leakage current	Vgs=-30V, Vps=0			1	nA
Drain current	Vps=10V, Vgs=0	1	4	12	mA
Cut off voltage	VDS=10V, I D=10 μA	-0.1		-3.0	V
Forward transfer admittance	VDS=10V, VGS=0, f=1kHz	6.0	15		mS
Forward transfer admittance	Vps=10V, I p=1mA, f=1kHz		8		mS
Output admittance	Vps=10V, Vgs=0, f=1kHz		10		μS
Input capacitance	VDS=10V, VGS=0, f=1MHz		20		pF
Noise figure	VDS=10V, I D=1mA, f=100Hz,Rg=1KΩ		1.0	2.5	dB
Drain to Sourse resistor	VDS=10mVrms(1kHz), VGS=0, I DSS=5mA		70		Ω
	Gate leakage current Drain current Cut off voltage Forward transfer admittance Forward transfer admittance Output admittance Input capacitance Noise figure	Gate leakage current Vgs=-30V, Vps=0 Drain current Vps=10V, Vgs=0 Cut off voltage Vps=10V, Vgs=0, f=1kHz Forward transfer admittance Vps=10V, Vgs=0, f=1kHz Vps=10V, Vgs=0, f=1kHz Output admittance Vps=10V, Vgs=0, f=1kHz Input capacitance Vps=10V, Vgs=0, f=1MHz Noise figure Vps=10V, Vgs=0, f=1MHz Vps=10V, Vgs=0, f=1MHz	MIN	PARAMETER TESTCONDITIONS MIN TYP Gate leakage current VGS=-30V, VDS=0 UDS=10V, VGS=0 1 4 Cut off voltage VDS=10V, I D=10 μA -0.1 Forward transfer admittance VDS=10V, VGS=0, f=1kHz 6.0 15 Forward transfer admittance VDS=10V, I D=1mA, f=1kHz 8 0 Output admittance VDS=10V, VGS=0, f=1kHz 10 Input capacitance VDS=10V, VGS=0, f=1MHz 20 Noise figure VDS=10V, I D=1mA, f=100Hz,RG=1KΩ 1.0	TESTCONDITIONS MIN TYP MAX

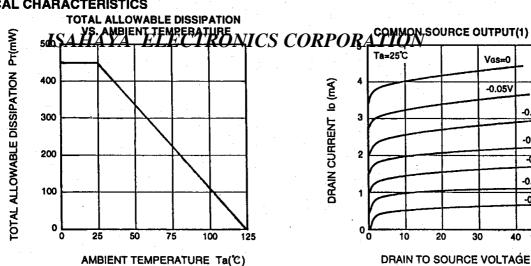
 ITEM
 C
 D
 E

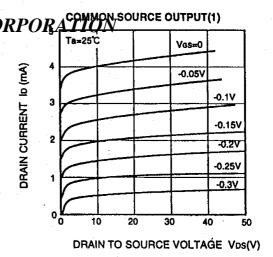
 I DSS
 1.0~3.0
 2.5~6.0
 5.0~12

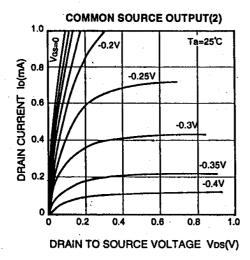
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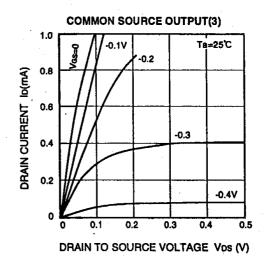
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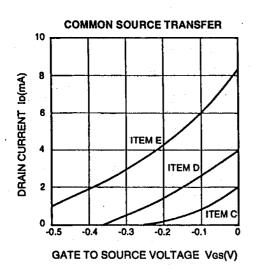
TYPICAL CHARACTERISTICS

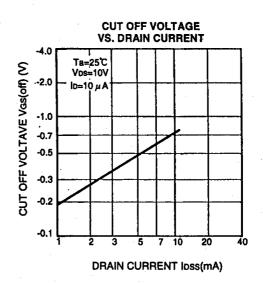








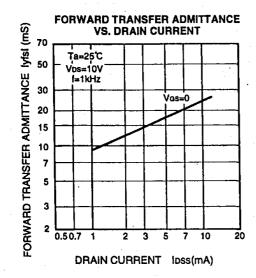


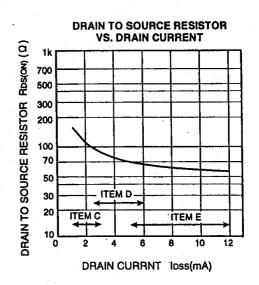


(Field-Effect Transistor)

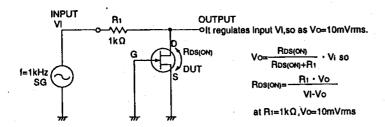
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For Low Frequency Amplify Application N Channel Junction type Micro(Frame type)





DRAIN TO SOURCE RESISTOR RDS(ON) TEST CIRCUIT





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